

Products

**10 kW Electron Beam Vapor Deposition System
(Thin Film Formation of Dielectric and Metal)**



The square chamber has the high vacuum pumping system, also incorporating the 10 kW electron gun and six switching type (manual) crucibles. The film forming process is performed in semi-automatic operation by the vapor deposition control system.

Features

1. Uniform film forming assured by the turning substrate holder capable of heating the substrate and adjusting the deposition angle.

Specifications

Substrate size	12 x 127 x 0.3 to 1.0t
Film forming speed	Max. 250 nm/min/AL (design value)
Film thickness uniformity	Within +/- 5%
Deposition source	10 kW
Substrate heating temperature	Max. 400 degrees C
Evacuating speed	Within 15 minutes to obtain x 10 ⁻⁴ Pa
Assist gas	3 types
Substrate turning speed	2 to 20 rpm
Substrate adjusting angle	0 to 90 degrees (manual adjustment)
Contact reference number	05D001